NSN 5962-01-330-5539

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-330-5539

Body Length:	
0.840 inches	
Body Width:	
Between 0.220 inche	s and 0.310 inches
Body Height:	
0.185 inches	
Maximum Power Di	ssipation Rating:
739.0 milliwatts	
Operating Tempura	ture Range:
-55.0/+125.0 degrees	s celsius
Storage Tempuratu	re Range:
-65.0/+150.0 degrees	s celsius
Features Provided:	
Bipolar and burn in a	nd monolithic and programmed and schottky and 3-state output
Inclosure Material:	
Ceramic	
Inclosure Configura	tion:
Dual-in-line	
Output Logic Form:	
Transistor-transistor I	ogic
Input Circuit Patterr	n:
6 input	
Case Outline Sourc	e And Designator:
D-2 mil-m-38510	
Terminal Surface Tr	eatment:
Solder	
Voltage Rating And	Type Per Characteristic:
7.0 volts power sour	ce
Time Rating Per Cha	acteristic:
80.00 nanoseconds	propagation delay time, low to high level output and 80.00 nanoseconds propagation delay time, high to low level
output	
Memory Device Typ	e:
Prom	
Test Data Documen	t:
96906-mil-std-883 sta	andard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And	Quantity:
16 printed circuit	
Shelf Life:	
N/a	
Unit Of Measure:	

Yes - demil/mli

NSN 5962-01-330-5539

Memory Microcircuit - Page 2 of 2

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